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[ZA/ZA]; Department of Physics, Rand Afrikaans University, Cnr Kingsway & University Roads, Auckland Park, 2006 Johannesburg (ZA).

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(74) Agent: **D M KISCH INC**; P O Box 781218, 2146 SAND-
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(71) Applicant (*for all designated States except US*): **RAND AFRIKAANS UNIVERSITY [ZA/ZA]**; Cnr Kingsway & University Roads, Auckland Park, 2006 Johannesburg (ZA).

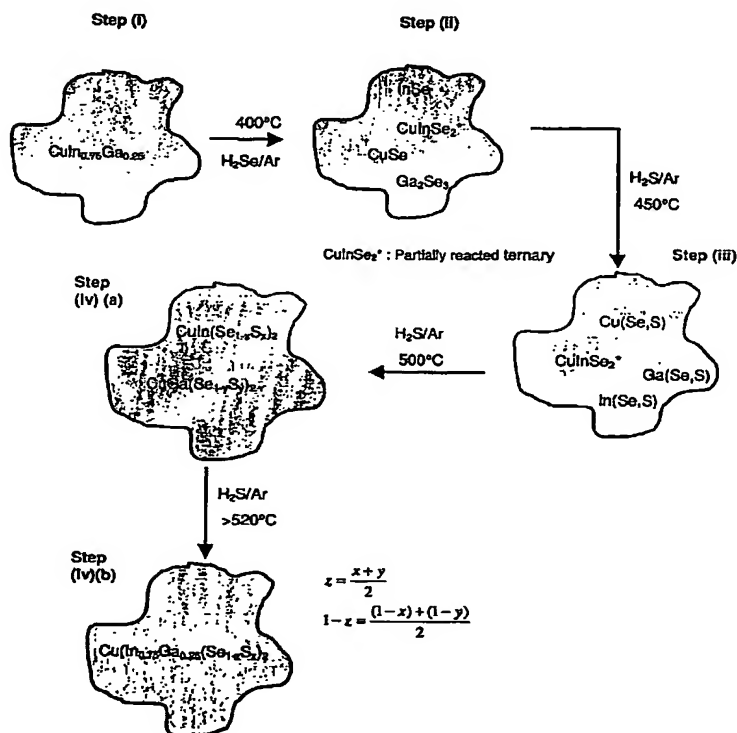
(72) Inventor; and

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(75) Inventor/Applicant (*for US only*): **ALBERTS, Vivian**

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(54) Title: METHOD FOR THE PREPARATION OF GROUP IB-III_A-VIA QUATERNARY OR HIGHER ALLOY SEMICONDUCTOR FILMS



(57) Abstract: This invention relates to a method for producing group IB-III_A-VIA quaternary or higher alloy semiconductor films wherein the method comprises the steps of (i) providing a metal film comprising a mixture of group IB and group III_A metals; (ii) heat treating the metal film in the presence of a source of a first group VIA element (said first group VIA element hereinafter being referred to as VIA₁) under conditions to form a first film comprising a mixture of at least one binary alloy selected from the group consisting of a group IB-VIA₁ alloy and a group III_A-VIA₁ alloy and at least one group IB-III_A-VIA₁ ternary alloy (iii) optionally heat treating the first film in the presence of a source of a second group VIA element (said second group VIA element hereinafter being referred to as VIA₂) under conditions to convert the first film into a second film comprising at least one alloy selected from the group consisting of a group IB-VIA₁-VIA₂ alloy and a group III_A-VIA₁-VIA₂ alloy; and the at least one group IB-III_A-VIA₁ ternary alloy of step (ii); (iv) heat treating either the first film or second film to form a group IB-III_A-VIA quaternary or higher alloy semiconductor film.



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